

Substitute for form 1449/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete if Known	
				Application Number	To Be Assigned <u>10/752705</u>
				Filing Date	January 8, 2004
				First Named Inventor	Takashi NOGUCHI et al.
				Art Unit	2813
				Examiner Name	Jack S. J. Chen
Sheet	1	of	1	Attorney Docket Number	SON-1285/DIV

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
JC	AA	5,155,571	10/13/1992	Wang et al.	
	AB	5,241,197	08/31/1993	Murakami et al.	
	AC	5,665,616 <u>9/97</u>	08/09/1997	Kimura et al.	
	AD	5,998,807	12/07/1999	Lustig et al.	
JC	AE	US2002/0011617 A1	01/31/2002	Kubo et al.	

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				
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NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
JC	CA	K. Ismail et al., "Electron transport properties of Si/SiGe heterostructures: Measurements and device Implications", Applied Physics Letters, Volume 63, August 2, 1993, Number 5, pgs. 660-662.	
	CB	L. H. Jiang, "Electrical Properties of GeSi Surface- and Buried- Channel p-MOSFET's Fabricated by Ge Implantation", IEEE Electron Devices, Volume 43, January 1996, Number 1, pgs. 97-103.	
	CC	K. Ismail et al., "High Pole Mobility In SiGe Alloys For Device Applications", Applied Physics Letters, Volume 64, June 6, 1994, Number 23, pgs. 3124-3126.	
JC	CD	J. Welser et al., "Strain Dependence of the Performance Enhancement in Strained-Si n-MOSFETs", Electron Devices Meeting, 1994, pgs. 373-376.	

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¹ Applicant's unique citation designation number (optional). ² Applicant is to place a check mark here if English language Translation is attached.

Examiner Signature	/Jack Chen/ (08/06/2006)	Date Considered	08/06/2006
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